Low Barrier Silicon Schottky Diodes



MSS30-xxx-x Series

Rev. V3

Features

- V_F, R_D and C_J Matching Options
- Chip, Beam Lead and Packaged Devices
- Hi-Rel Screening per MIL-PRF-19500 and MIL-PRF-38534 Available

Description

The MSS30-xxx-x Series of Schottky diodes are fabricated on N-Type epitaxial substrates using proprietary processes that yield the highest FCOs in the industry. Optimum mixer performance is obtained with LO power of -3 dBm to +3 dBm per diode.



Chip

Electrical Specifications: T_A = 25°C

Model	Configuration	V _F Typ. V	V _{BR} Min. V	C _J Typ. / Max. pF	R _s Typ. Ω	R _D Max. Ω	F _{co} Typ. GHz	Outline
MSS30-046-C15	Single Junction	0.29	2	0.10 / 0.12	10	18	160	C15
MSS30-050-C15	Single Junction	0.27	2	0.15 / 0.18	6	15	175	C15
Test Conditions		I _F = 1 mA	I _R = 10 μA	$V_R = 0 V$ F = 1 MHz	I = 5	mA		

Beam Lead

Electrical Specifications: T_A = 25°C

Model	Configuration	V _F Typ. V	V _{BR} Min. V	C _J Typ. / Max. pF	R _s Typ. Ω	R _D Max. Ω	F _{co} Typ. GHz	Outline
MSS30-142-B10B	Single Junction	0.29	2	0.07 / 0.10	13	22	175	B10B
MSS30-148-B10B	Single Junction	0.27	2	0.12 / 0.15	7	15	190	B10B
MSS30-154-B10B	Single Junction	0.25	2	0.22 / 0.25	3	12	240	B10B
MSS30-242-B20	Series Tee	0.29	2	0.07 / 0.10	13	22	175	B20
MSS30-248-B20	Series Tee	0.27	2	0.12 / 0.15	7	15	190	B20
MSS30-254-B20	Series Tee	0.25	2	0.22 / 0.25	3	12	240	B20
MSS30-346-B21	Anti Parallel Pair	0.27	-	0.27 / 0.30	11	16	55	B21
MSS30-442-B41	Ring Quad	0.29	2	0.07 / 0.10	13	22	175	B41
MSS30-448-B41	Ring Quad	0.27	2	0.12 / 0.15	7	15	190	B41
MSS30-454-B40	Ring Quad	0.25	2	0.22 / 0.25	3	12	240	B40
Test Conditions		I _F = 1 mA	I _R = 10 μA	$V_R = 0 V$ F = 1 MHz	l = 5	mA		

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Packaged

Electrical Specifications: T_A = 25°C

Model	Configuration	V _F Typ. V	V _{BR} Min. V	C _T Typ. / Max. pF	R _s Typ. Ω	R _D Max. Ω	F _{co} Typ. GHz	Outline
MSS30-046-P55	Single Junction	0.29	2	0.23 / 0.30	10	18	160	P55
MSS30-046-P86	Single Junction	0.29	2	0.27 / 0.33	10	18	160	P86
MSS30-050-P55	Single Junction	0.27	2	0.28 / 0.35	6	15	175	P55
MSS30-050-P86	Single Junction	0.27	2	0.32 / 0.38	6	15	175	P86
MSS30-142-E25	Single Junction	0.29	2	0.20 / 0.26	13	22	175	E25
MSS30-142-H20	Single Junction	0.29	2	0.25 / 0.31	13	22	175	H20
MSS30-148-E25	Single Junction	0.27	2	0.25 / 0.31	7	15	190	E25
MSS30-148-H20	Single Junction	0.27	2	0.30 / 0.36	7	15	190	H20
MSS30-154-E25	Single Junction	0.25	2	0.35 / 0.41	3	12	240	E25
MSS30-154-H20	Single Junction	0.25	2	0.40 / 0.46	3	12	240	H20
MSS30-242-E35	Series Tee	0.29	2	0.15 / 0.21	13	22	175	E35
MSS30-242-H30	Series Tee	0.29	2	0.25 / 0.31	13	22	175	H30
MSS30-248-E35	Series Tee	0.27	2	0.25 / 0.31	7	15	190	E35
MSS30-248-H30	Series Tee	0.27	2	0.30 / 0.36	7	15	190	H30
MSS30-254-E35	Series Tee	0.25	2	0.35 / 0.41	3	12	240	E35
MSS30-254-H30	Series Tee	0.25	2	0.40 / 0.46	3	12	240	H30
MSS30-346-E25	Anti-Parallel Pair	0.27	-	0.35 / 0.40	11	16	55	E25
MSS30-346-H20	Anti-Parallel Pair	0.27	-	0.45 / 0.50	11	16	55	H20
MSS30-442-E45	Ring Quad	0.29	2	0.15 / 0.21	13	22	175	E45
MSS30-448-E45	Ring Quad	0.27	2	0.20 / 0.26	7	15	190	E45
MSS30-454-E45	Ring Quad	0.25	2	0.25 / 0.31	3	12	240	E45
MSS30-454-H40	Ring Quad	0.25	2	0.25 / 0.31	3	12	240	H40
Test Conditions		I _F = 1 mA	I _R = 10 μA	$V_R = 0 V$ F = 1 MHz	I = 5	i mA		

Absolute Maximum Ratings

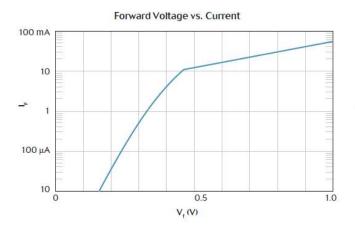
Parameters	Rating				
Reverse Voltage	Rated V _{BR}				
Forward Current	50 mA				
Power Dissipation	100 mW, per junction @ T_A = 25°C, derate linearly to 0 @ T_A = +150°C				
Operating Temperature	-65°C to +150°C				
Storage Temperature	-65°C to +150°C				
Soldering Temperature (packaged)	+230°C for 5 seconds				
Beam Lead Pull Strength	4 G minimum				

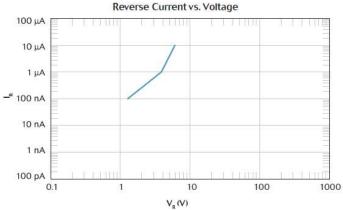


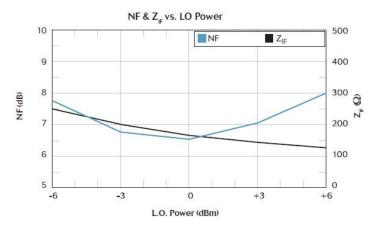
MSS30-xxx-x Series

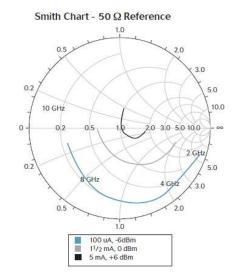
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Typical Performance Curves: T_A = 25°C









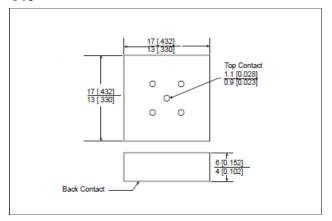


MSS30-xxx-x Series

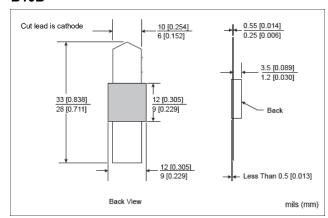
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Outline Drawings

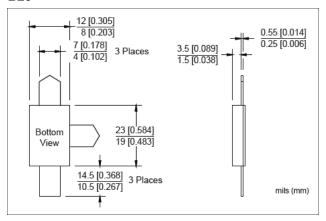
C15



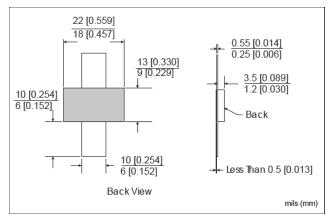
B10B



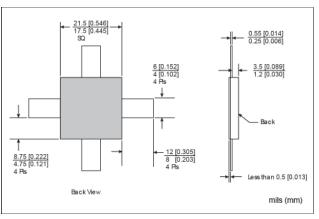
B20



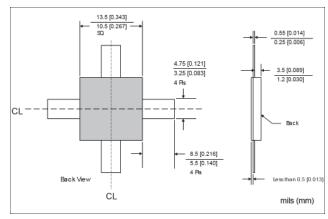
B21



B40



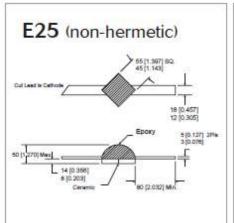
B41

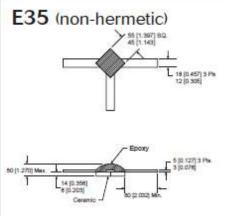


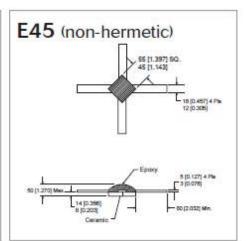


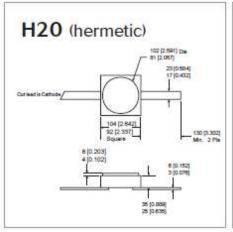
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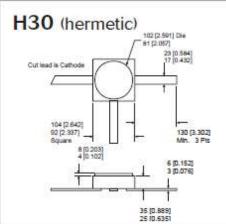
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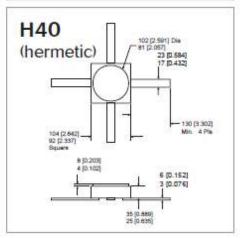


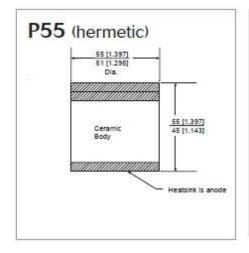


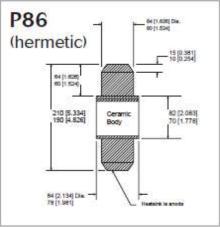












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Rev. V3

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